



INTERNAL NTC - THERMISTOR SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	UNITS
Resistance	R_{25}	$T_C = 25\text{ }^\circ\text{C}$	5000	Ω
	R_{100}	$T_C = 100\text{ }^\circ\text{C}$	$493 \pm 5\%$	
B-value	$B_{25/50}$	$R_2 = R_{25} \exp [B_{25/50} (1/T_2 - 1/(298.15K))]$	$3375 \pm 5\%$	K
Maximum operating temperature			220	$^\circ\text{C}$
Dissipation constant			2	mW/ $^\circ\text{C}$
Thermal time constant			8	s

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
IGBT - junction-to-case (per switch)	R_{thJC}	-	-	0.2	$^\circ\text{C}/\text{W}$
DIODE - junction-to-case (per diode)	R_{thJC}	-	-	0.46	
Case to sink, flat, greased surface (per module)	R_{thJS}	-	0.015	-	
Mounting torque (M5)		3.0	-	6.0	Nm
Weight		-	285	-	g

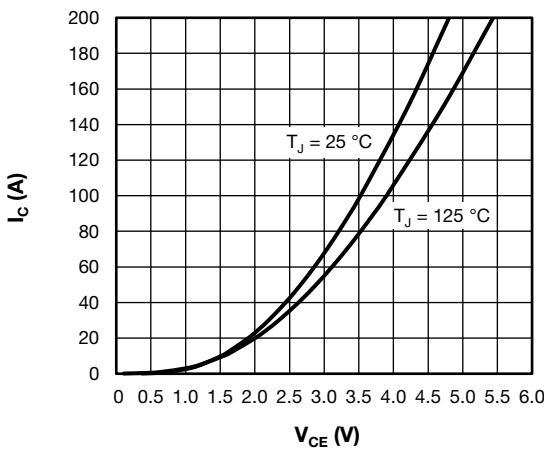


Fig. 1 - Typical IGBT Output Characteristics, $V_{GE} = 15\text{ V}$

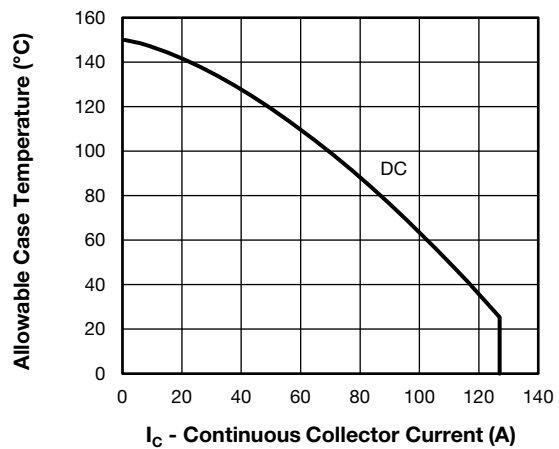


Fig. 3 - Maximum IGBT Continuous Collector Current vs. Case Temperature

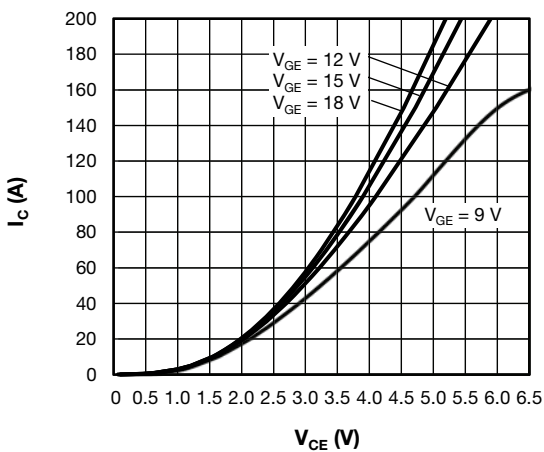


Fig. 2 - Typical IGBT Output Characteristics, $T_J = 125\text{ }^\circ\text{C}$

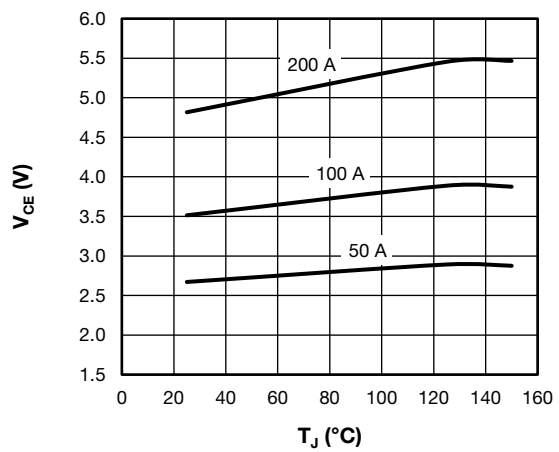


Fig. 4 - Collector to Emitter Voltage vs. Junction Temperature

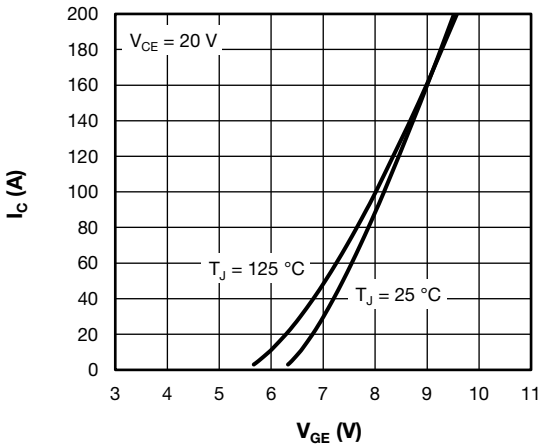


Fig. 5 - Typical IGBT Transfer Characteristics

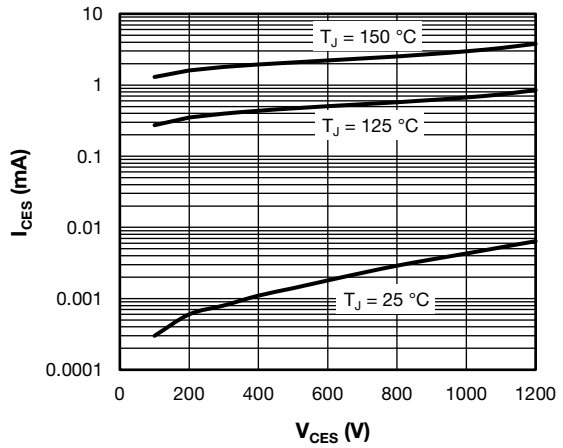


Fig. 8 - Typical IGBT Zero Gate Voltage Collector Current

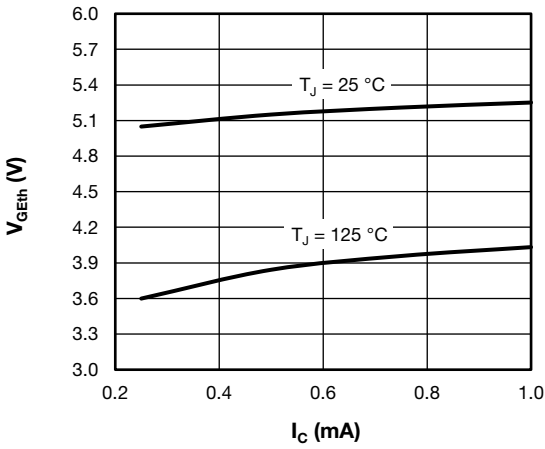


Fig. 6 - Typical IGBT Gate Threshold Voltage

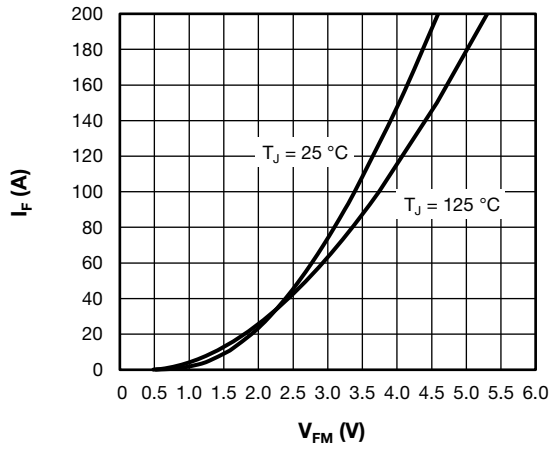


Fig. 9 - Typical Diode Forward Characteristics

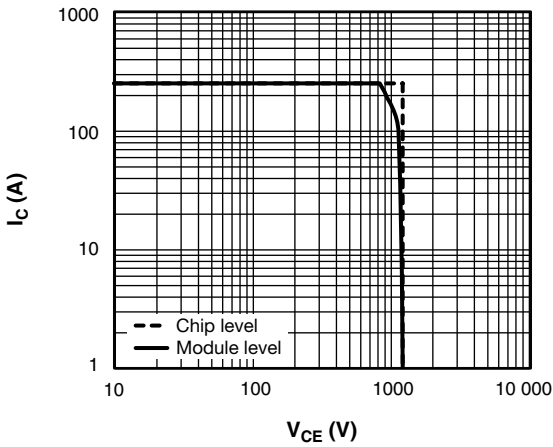


Fig. 7 - IGBT Reverse BIAS SOA $T_J = 150\text{ }^\circ\text{C}$, $V_{GE} = 15\text{ V}$

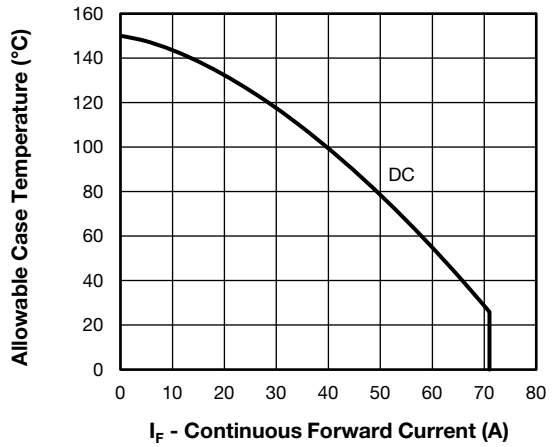


Fig. 10 - Maximum Diode Continuous Forward Current vs. Case Temperature